

Lecture 14

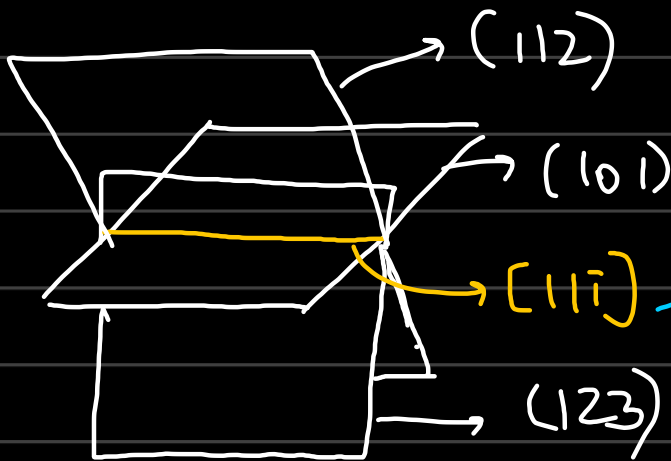
Dislocation in hcp:

burgers vector

$$\frac{a_0}{3} [11\bar{2}0] \rightarrow \frac{a_0}{3} [10\bar{1}0] + \frac{a_0}{3} [01\bar{1}0]$$

↳ Slip occurs on basal plane (0001) in the $[11\bar{2}0]$ direction.

Dislocation in bcc:

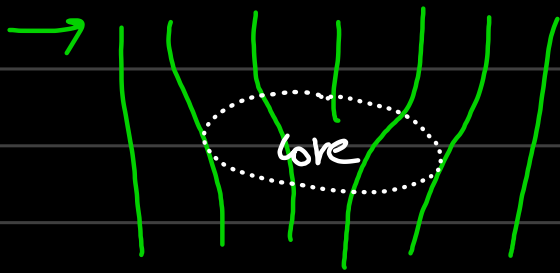
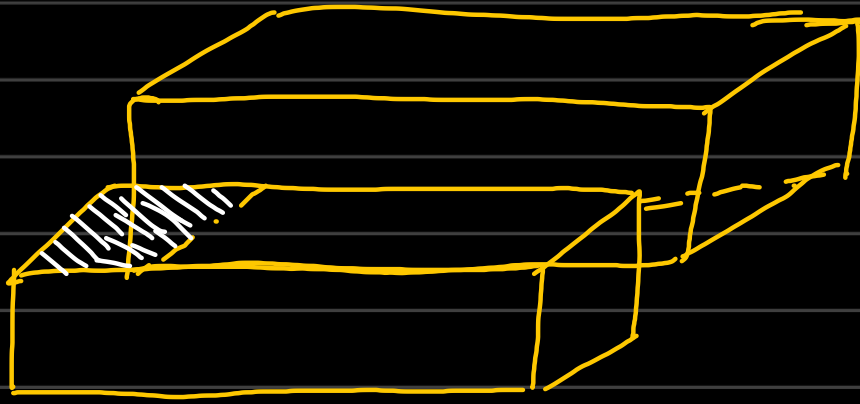


→ Slip bands in bcc:
↳ Wavy glide
{wavy slip, pencil slip}.

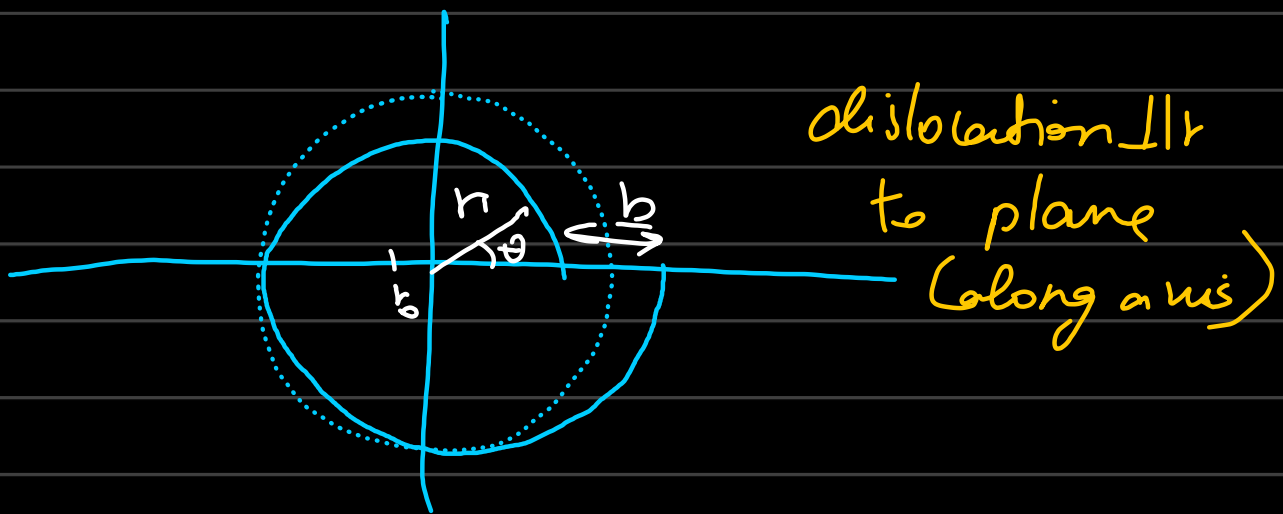
burgers vector in bcc

* glide slip in bcc called pencil glide.

Strain field about dislocations:-



→ Stress field about dislocation is *elastic*.



→ can be considered as a plane strain condition

$$\star \quad \sigma_r = \sigma_\theta = -\frac{\tau_0 b \sin \theta}{r}$$

$$\tau_{r\theta} = \tau_{\theta r} = \frac{\tau_0 b \cos \theta}{r}$$

$$\tau_0 = \frac{G}{2\pi(1-\nu)}$$

★ Due to $\tau \rightarrow \infty$ as $r \rightarrow 0$, a small cylinder of $r=r_0$ will be excluded from analysis.

★ The strain energy involved in formation of an edge dislocations.

G estimated work done to displace the cut OA along slip plane.

$$U = \frac{1}{2} \int_{r_0}^{r_1} \tau_{r\theta} b dr = \frac{1}{2} \int_{r_0}^{r_1} \tau_0 b \cos \theta \frac{dr}{r}$$

$$U = \frac{Gb^2}{4\pi(1-\nu)} \ln\left(\frac{r_1}{r_0}\right)$$

Total Strain energy = Elastic SE + Energy of the core

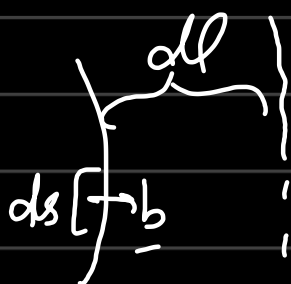
→ In screw dislocations: no normal stresses
 ↳ only shear stresses involved.

$$\tau_{\theta z} = \frac{Gb}{2\pi r} \quad U = \frac{1}{2} \int_{r_0}^h \tau_{\theta z} b dr = \frac{Gb^2 \ln\left(\frac{r_1}{r_0}\right)}{4\pi}$$

✧ For typical annealed crystals:
 $r_1 = 100 \text{ nm}$, $b = 0.2 \text{ nm}$

$$\ln\left(\frac{r_1}{b}\right) \approx 2\pi \quad \text{✧ Dislocation energy per unit length} \Rightarrow U = \frac{Gb^2}{2}$$

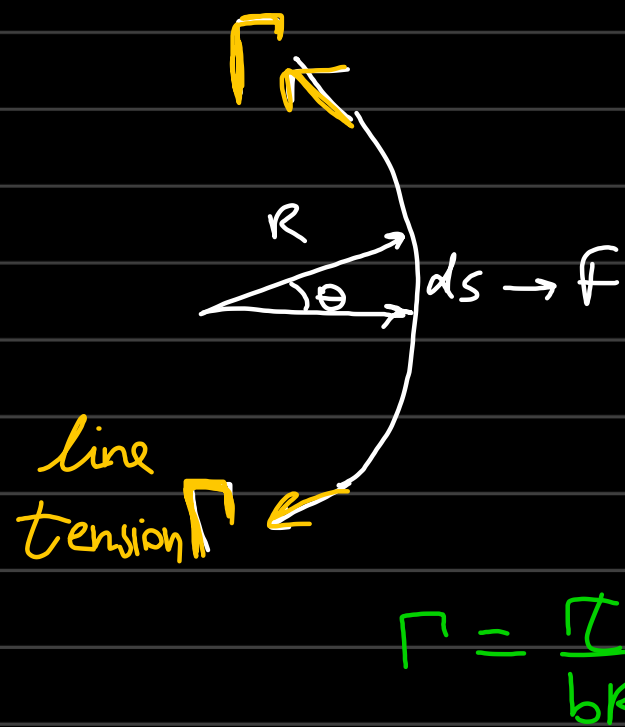
✧ Forces on a dislocation:



↙ force per unit length

$$F = \frac{dW}{dl ds} = \tau b$$

↳ This force is normal to the dislocation line at every point and directed towards unslipped plane.



$$F = \Gamma b$$

$$R d\theta ds$$

$$\Gamma d\theta = \Gamma b ds$$

$$\Gamma = \frac{Gb}{2R}$$

$$\Gamma = \frac{\tau}{bR}$$

Force per unit length $\Rightarrow \frac{Gb^2}{2R}$

* The radial force F_r between two parallel screw dislocations:

$$F_r = \tau_{\theta z} b = \frac{Gb^2}{2\pi r}$$

distance b/w dislocations.

→ For edge dislocations:

$$F_r =$$

$$F_\theta =$$

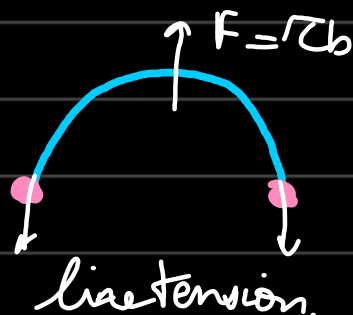
Dislocation Generation:

- Study finds that the macroscopic step created on surface of crystal is not the sum of all burgers vector of inherent dislocations
- This suggests that there are sources in crystal which get activated due to plastic deformation and generate additional dislocations.
- ↳ This generation of new dislocation allows to maintain geometric coherence of crystals.

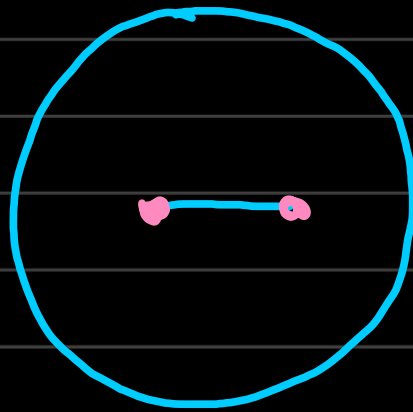
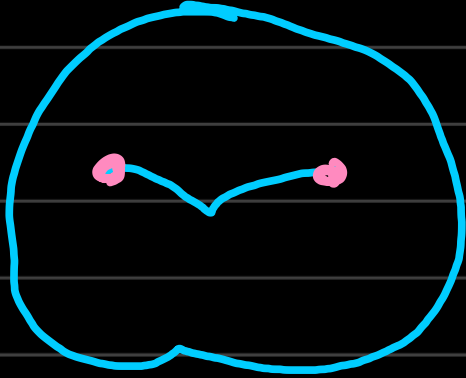
Dislocation Sources:

- i> shear stress exerts $F = \tau b$ on dislocation line which is pinned on both ends.

{ Frank-Read Source }

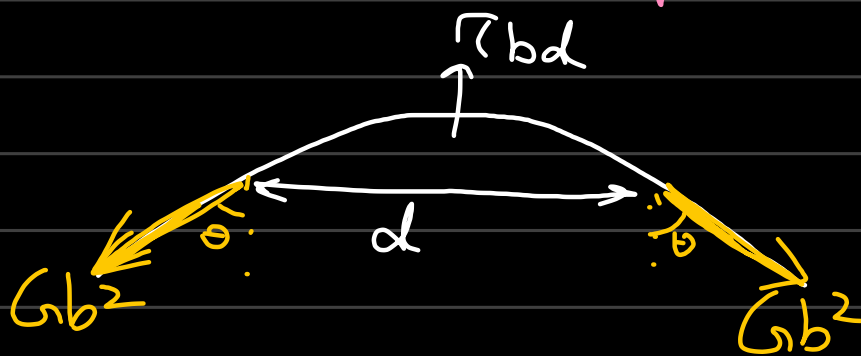


- shear stress maximum when segment becomes semicircle.



→ series of concentric dislocation loops are formed.

Minimum stress to operate F-R source.



$$\star \quad \tau_{bd} = 2Gb^2 \quad \Rightarrow \quad \boxed{\tau = \frac{2Gb}{d}} \quad \text{when } \theta = 90^\circ$$

$\star \quad \rho = \frac{1}{d^2}$ { dislocation density vs dist b/w dislocations }

$$\boxed{\tau = 2Gb\sqrt{\rho}}$$

→ Statistical quantity
{ d cannot be estimated
 ρ can be estimated }

→ Hall-petch relation:-

$$\tau_c = \frac{\pi (\tau - \tau_i)^2 D}{4Gb}$$

$$\tau = \tau_i + \left(\frac{\tau_c 4Gb}{\pi D} \right)^{1/2} = \tau_i + k' D^{-1/2}$$

$$\sigma_0 = \sigma_i + k D^{-1/2}$$

↓
yield strength

↓

↪ locking parameter:

friction stress: overall resistance of the crystal lattice to dislocation movement.

Inverse Hall-petch relation:

↳ post theoretical limit,

* Hall-petch relation is valid under the assumption that there are at least $\langle N \rangle \geq 50$ 50 dislocations at the pileup near grain boundary.

Recovery and Recrystallization:-

Cold work $\left\{ \begin{array}{l} \xrightarrow{\text{low } T} \text{ recovery} \\ \xrightarrow{\text{high } T} \text{ recrystallization.} \end{array} \right.$

↳ dynamic recovery & dynamic recrystallization.